

CMOS Hex Buffer

High-Voltage Types (20-Volt Rating)

3-State Non-Inverting Type

■ CD4503B is a hex noninverting buffer with 3-state outputs having high sink- and source-current capability. Two disable controls are provided, one of which controls four buffers and the other controls the remaining two buffers. The CD4503B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

- 1 TTL-load output drive capability
- 2 output-disable controls
- 3-state outputs
- Pin compatible with industry types MM80C97, MC14503, and 340097
- 5-V, 10-V, and 15-V parametric ratings
- Maximum input current of $1\ \mu\text{A}$ at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- 3-state hex buffer for interfacing IC's with data buses
- CMOS to TTL hex buffer

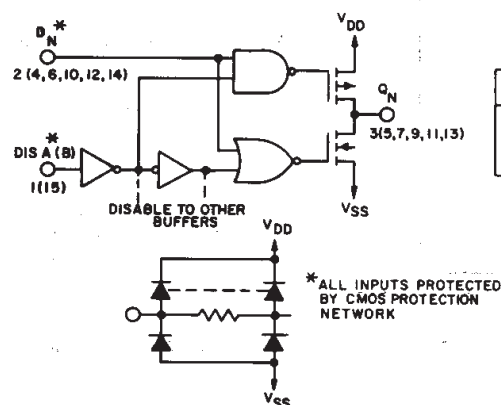


Fig. 1—Logic diagram of 1 to 6 identical buffers.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})

Voltages referenced to V_{SS} Terminal) -0.5V to $+20\text{V}$

INPUT VOLTAGE RANGE, ALL INPUTS -0.5V to $V_{DD} + 0.5\text{V}$

DC INPUT CURRENT, ANY ONE INPUT $\pm 10\text{mA}$

POWER DISSIPATION PER PACKAGE (P_D):

For $T_A = -55^\circ\text{C}$ to $+100^\circ\text{C}$ 500mW

For $T_A = +100^\circ\text{C}$ to $+125^\circ\text{C}$ Derate Linearly at $12\text{mW}/^\circ\text{C}$ to 200mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$ 100mW

OPERATING-TEMPERATURE RANGE (T_A) -55°C to $+125^\circ\text{C}$

STORAGE TEMPERATURE RANGE (T_{stg}) -65°C to $+150^\circ\text{C}$

LEAD TEMPERATURE (DURING SOLDERING):

At distance $1/16 \pm 1/32$ inch ($1.59 \pm 0.79\text{mm}$) from case for 10s max $+265^\circ\text{C}$

CD4503B Types

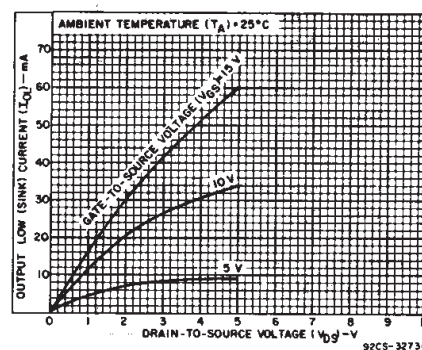
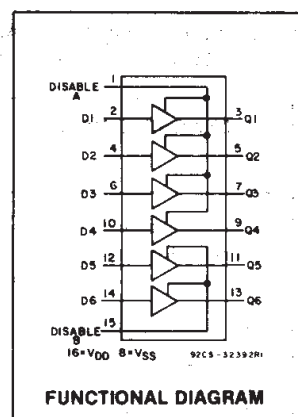


Fig. 2—Typical n-channel output low (sink) current characteristics.

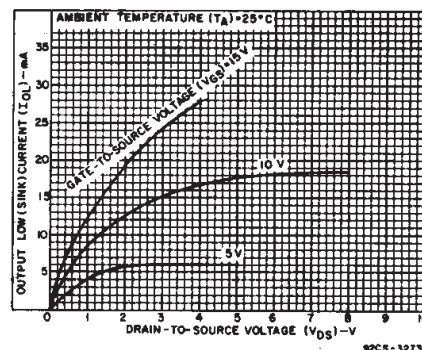
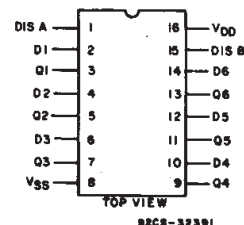


Fig. 3—Minimum n-channel output low (sink) current characteristics.



TERMINAL ASSIGNMENT

CD4503B Types

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25			
								Min.	Typ.	Max.	
Quiescent Device	—	0,5	5	1	1	30	30	—	0.02	1	μA
	—	0,10	10	2	2	60	60	—	0.02	2	
Current, I _{DD} Max.	—	0,15	15	4	4	120	120	—	0.02	4	
	—	0,20	20	20	20	600	600	—	0.04	20	
Output Low (Sink) Current I _{OL} Min.	0.4	0	5	2.6	2.5	1.4	1.3	2.1	2.3	—	mA
	0.5	0	10	6.5	6.4	3.9	3.8	5.5	6.2	—	
	1.5	0	15	19.2	18.9	11.4	11.2	16.1	23	—	
Output High (Source) Current, I _{OH} Min.	4.6	5	5	-1.2	-1.16	-0.7	-0.7	-1.02	-1.9	—	
	2.5	5	5	-5.8	-5.7	-3.4	-3	-4.8	-6.1	—	
	9.5	10	10	-3.1	-3	-1.9	-1.8	-2.6	-3.7	—	
	13.5	15	15	-8.2	-8	-4.9	-4.8	-6.8	-14.1	—	
Output Voltage: Low-Level, V _{OL} Max.	—	0,5	5	0.05				—	0	0.05	V
	—	0,10	10	0.05				—	0	0.05	
	—	0,15	15	0.05				—	0	0.05	
Output Voltage: High-Level, V _{OH} Min.	—	0,5	5	4.95				4.95	5	—	
	—	0,10	10	9.95				9.95	10	—	
	—	0,15	15	14.95				14.95	15	—	
Input Low Voltage, V _{IL} Max.	0.5,4.5	—	5	1.5				—	—	1.5	V
	1,9	—	10	3				—	—	3	
	1.5,13.5	—	15	4				—	—	4	
Input High Voltage, V _{IH} Min.	0.5,4.5	—	5	3.5				3.5	—	—	
	1,9	—	10	7				7	—	—	
	1.5,13.5	—	15	11				11	—	—	
Input Current I _{IN} Max.	—	0,18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA
3-State Output Leakage Current, I _{OUT} Max.	0,18	0,18	18	±0.4	±0.4	±12	±12	—	±10 ⁻⁴	±0.4	

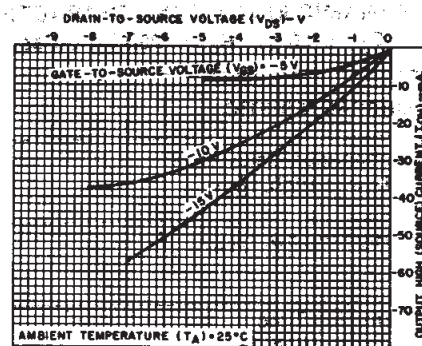


Fig. 4—Typical p-channel output high (source) current characteristics.

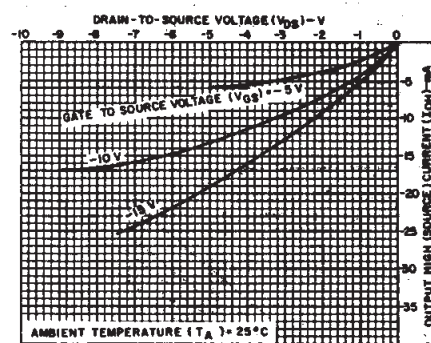


Fig. 5—Minimum p-channel output high (source) current characteristics.

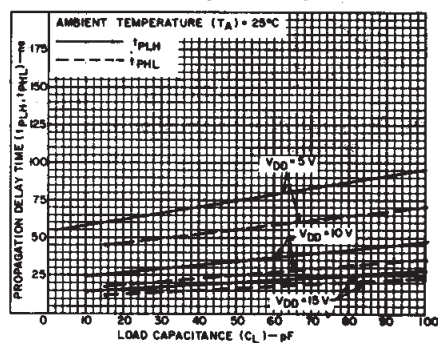


Fig. 6—Typical propagation delay time as a function of load capacitance.

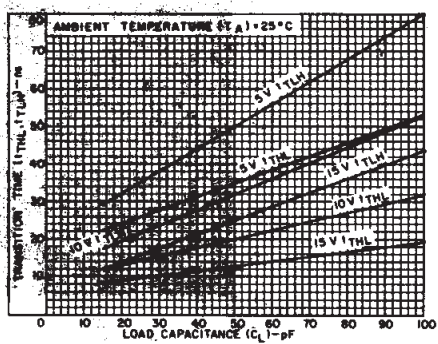


Fig. 7—Typical transition time as a function of load capacitance.

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply-Voltage Range (For T _A = Full Package-Temperature Range)	3	18	V

CD4503B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$; input $t_r, t_f = 20\text{ ns}$,
 $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$ unless otherwise specified.

CHARACTERISTIC	V_{DD} (V)	LIMITS		UNITS
		Typ.	Max.	
Propagation Delay Time: Low-to-High, t_{PLH}	5	75	150	ns
	10	35	70	
	15	25	50	
High-to-Low, t_{PHL}	5	55	110	ns
	10	25	50	
	15	17	35	
Transition Time: Low-to-High, t_{TLH}	5	50	90	ns
	10	30	45	
	15	25	35	
High-to-Low, t_{THL}	5	35	70	ns
	10	20	40	
	15	13	25	
3-State Propagation Delay Time: $R_L = 1\text{ k}\Omega$ t_{PHZ}, t_{PZH}	5	70	140	ns
	10	30	60	
	15	25	50	
t_{PZL}, t_{PLZ}	5	90	180	ns
	10	40	80	
	15	35	70	

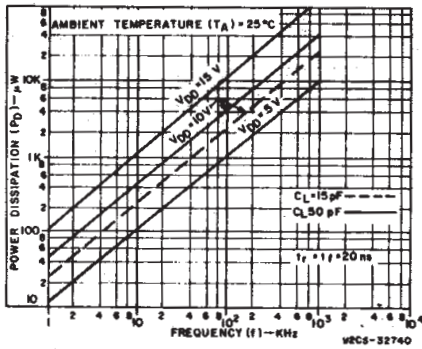


Fig. 8—Typical power dissipation as a function of frequency.

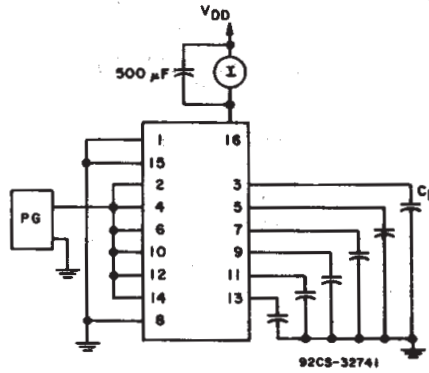


Fig. 9—Dynamic power dissipation test circuit.

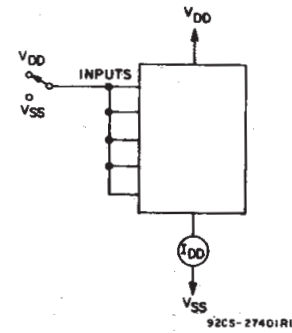


Fig. 10—Quiescent device current test circuit.

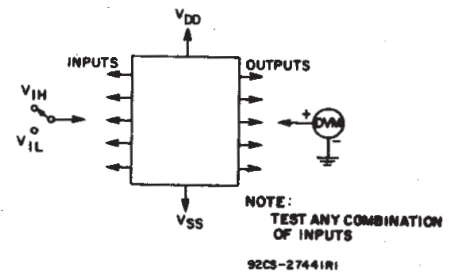


Fig. 11—Input voltage test circuit.

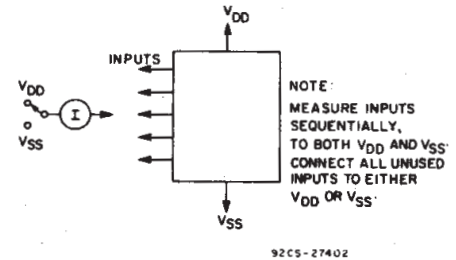
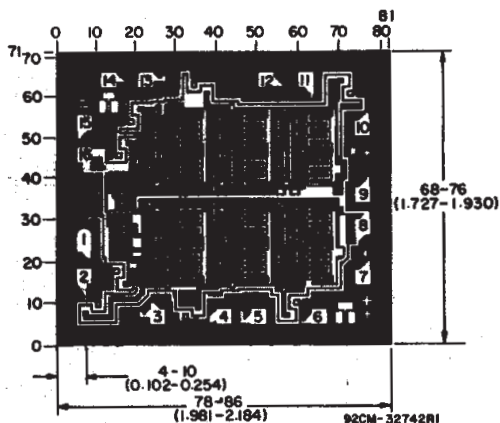


Fig. 12—Input current test circuit.



Dimensions and pad layout for CD4503BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

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